

MOSFETs Silicon P-Channel MOS (U-MOSVI)

XPH8R316MC

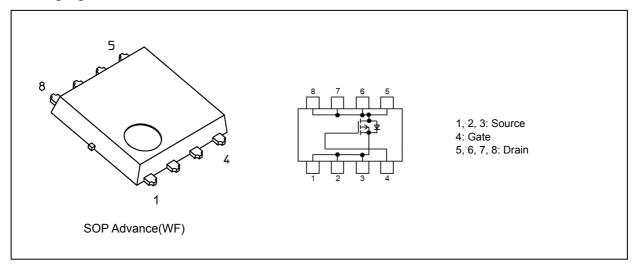
1. Applications

- · Automotive
- · Switching Voltage Regulators
- · DC-DC Converters
- · Motor Drivers

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 6.4 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = -10 \mu A (max) (V_{DS} = -60 V)$
- (5) Enhancement mode: V_{th} = -1.0 to -2.1 V (V_{DS} = -10 V, I_D = -1 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteris	tics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	-60	V
Gate-source voltage		(Note 1)	V _{GSS}	+10/-20	
Drain current (DC)		(Note 2)	I _D	-90	Α
Drain current (pulsed)		(Note 2)	I _{DP}	-180	
Power dissipation	(T _c = 25 °C)		P _D	170	W
Power dissipation	(t = 10 s)	(Note 3)]	3	
Power dissipation	(t = 10 s)	(Note 4)		0.96	
Single-pulse avalanche energy		(Note 5)	E _{AS}	126	mJ
Single-pulse avalanche current			I _{AS}	-90	Α
Channel temperature		(Note 6)	T _{ch}	175	°C
Storage temperature		(Note 6)	T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: AEC-Q101 qualification is performed at V_{GS} = 8/-20 V, Ta=175°C

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T _c = 25 °C)		Z _{th(ch-c)}	0.88	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z _{th(ch-a)}	50	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 4)	Z _{th(ch-a)}	156	

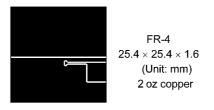
Note 2: Ensure that the channel temperature does not exceed 175 °C.

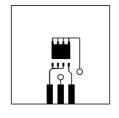
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = -48 V, T_{ch} = 25 °C (initial), L = 12 μ H, R_{G} = 25 Ω , I_{AS} = -90 A, V_{GS} = 0/-15 V

Note 6: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy
Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{GS} = +10/-20 V, V _{DS} = 0 V	_	_	±1	μА
Drain cut-off current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$			-10	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60			V
	V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$	-50	_		
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-1.0	_	-2.1	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = -4.5 \text{ V}, I_D = -45 \text{ A}$	_	6.8	10.2	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -45 \text{ A}$		6.4	8.3	

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 300 kHz	_	10500	14700	pF
Reverse transfer capacitance	C _{rss}		_	740	1036	
Output capacitance	C _{oss}		_	860		
Gate resistance	r _g		_	13	26	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	115		ns
Switching time (turn-on time)	t _{on}		_	125		
Switching time (fall time)	t _f		_	436	_	
Switching time (turn-off time)	t _{off}		_	1890	_	

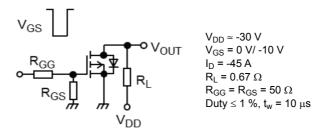


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -48 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -90 \text{ A}$	_	222		nC
Gate-source charge 1	Q _{gs1}		_	19		
Gate-drain charge	Q_{gd}		_	47		

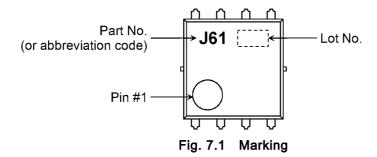
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 7)	I _{DR}	_	_	_	-90	Α
Reverse drain current (pulsed)	(Note 7)	I _{DRP}	_	_		-180	Α
Diode forward voltage		V_{DSF}	I _{DR} = -90 A, V _{GS} = 0 V	_	_	1.2	V
Reverse recovery time		t _{rr}	I _{DR} = -90 A, V _{GS} = 0 V	_	113	_	ns
Reverse recovery charge	·	Q_{rr}	-dI _{DR} /dt = -50 A/μs		90		nC

Note 7: Ensure that the channel temperature does not exceed 175 $^{\circ}\text{C}.$

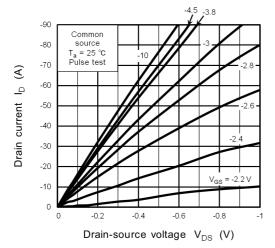


7. Marking





8. Characteristics Curves (Note)





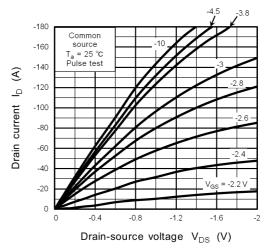


Fig. 8.2 I_D - V_{DS}

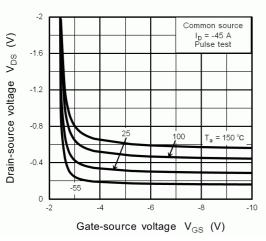


Fig. 8.3 V_{DS} - V_{GS}

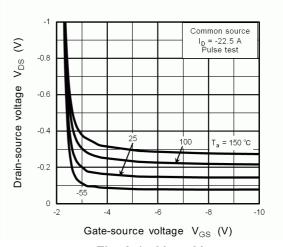


Fig. 8.4 VDS - VGS

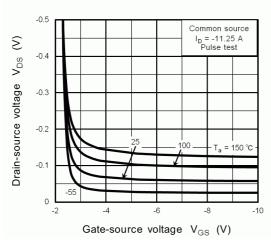


Fig. 8.5 V_{DS} - V_{GS}

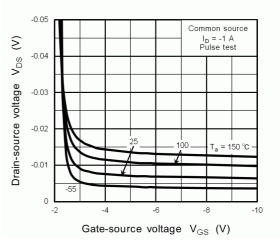


Fig. 8.6 V_{DS} - V_{GS}



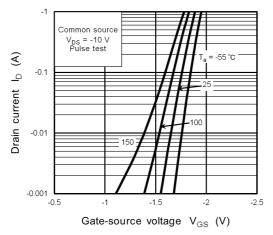


Fig. 8.7 ID - VGS

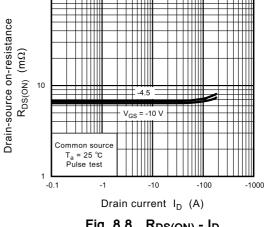


Fig. 8.8 RDS(ON) - ID

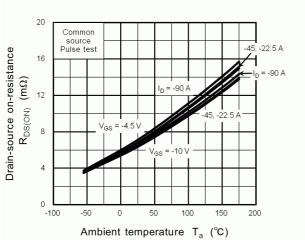


Fig. 8.9 R_{DS(ON)} - T_a

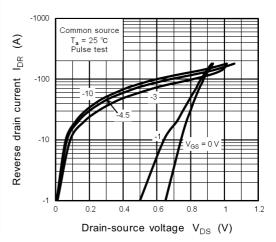


Fig. 8.10 I_{DR} - V_{DS}

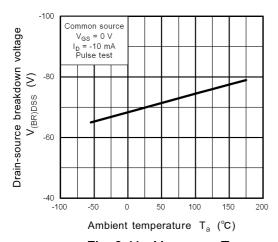


Fig. 8.11 V_{(BR)DSS} - T_a

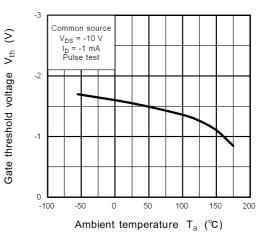


Fig. 8.12 V_{th} - T_a



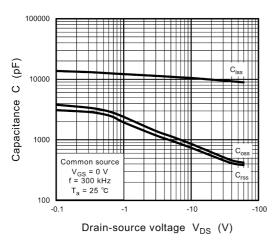


Fig. 8.13 Capacitance - V_{DS}

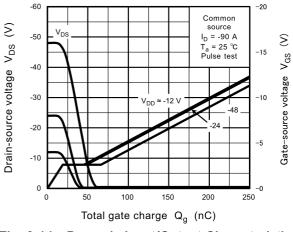


Fig. 8.14 Dynamic Input/Output Characteristics

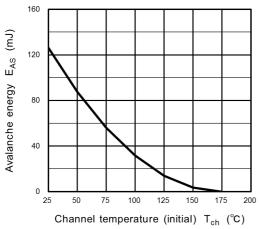


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

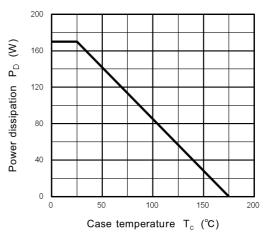
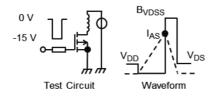


Fig. 8.16 P_D - T_c (Guaranteed Maximum)



$$\begin{aligned} &R_{G} = 25 \; \Omega \\ &V_{DD} = -48 \; V, \, L = 12 \; \mu H \end{aligned} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^{2} \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

Fig. 8.17 Test Circuit/Waveform



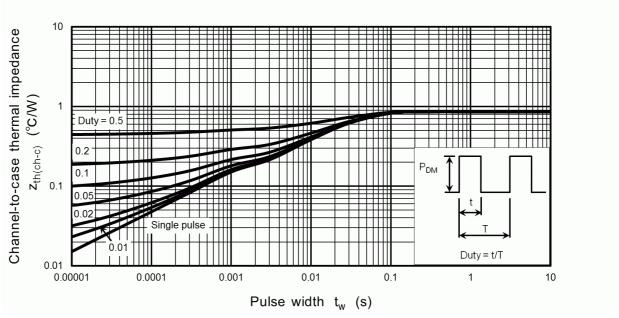


Fig. 8.18 $z_{th(ch-c)}$ - t_w (Guaranteed Maximum)

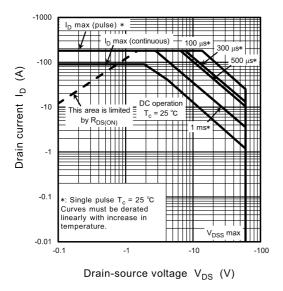


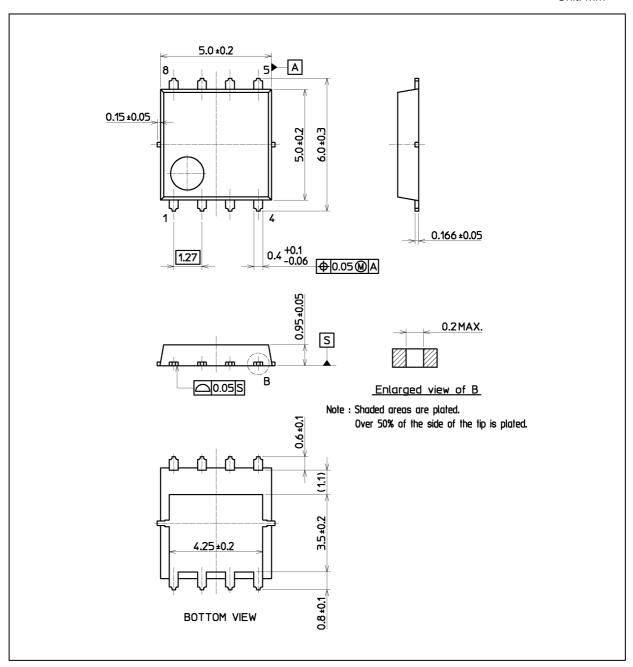
Fig. 8.19 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.083 g (typ.)

Package Name(s)
TOSHIBA: 2-5Q4A
Nickname: SOP Advance(WF)



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